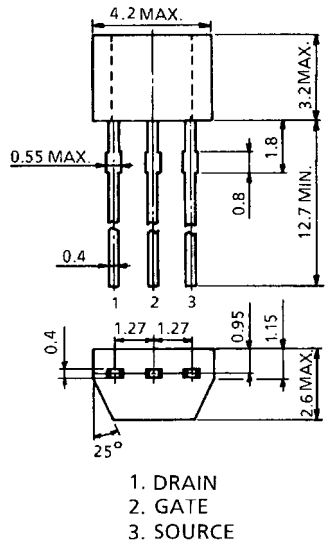
TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK372

For Audio Amplifier, Analog-Switch, Constant Current and Impedance Converter Applications

- High breakdown voltage: V_{GDS} = −40 V
- High input impedance: I_{GSS} = −1.0 nA (max) (V_{GS} = −30 V)
- Low $R_{DS\ (ON)}$: $R_{DS\ (ON)}$ = 20 Ω (typ.) (I_{DSS} = 15 mA)
- Small package

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-4E1C

Weight: 0.13 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	−40	V
Gate current	I_G	10	mA
Drain power dissipation	P_D	200	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

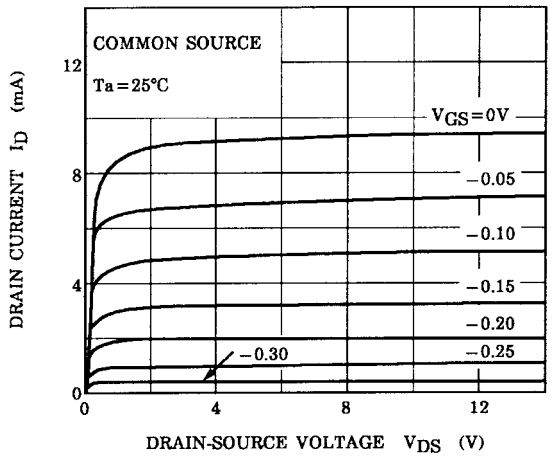
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	I_{GSS}	V_{GS} = −30 V, V_{DS} = 0	—	—	−1.0	nA
Gate-drain breakdown voltage	$V_{(BR)\ GDS}$	V_{DS} = 0, I_G = −100 μA	−40	—	—	V
Drain current	I_{DSS} (Note 1)	V_{DS} = 10 V, V_{GS} = 0	5.0	—	30	mA
Gate-source cut-off voltage	$V_{GS\ (OFF)}$	V_{DS} = 10 V, I_D = 0.1 μA	−0.3	—	−1.2	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 10 V, V_{GS} = 0, f = 1 kHz (Note 2)	25	60	—	mS
Input capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz	—	75	—	pF
Reverse transfer capacitance	C_{rss}	V_{DG} = 10 V, I_D = 0, f = 1 MHz	—	15	—	pF
Drain-source ON resistance	$R_{DS\ (ON)}$	V_{DS} = 10 mV, V_{GS} = 0 (Note 2)	—	20	—	Ω

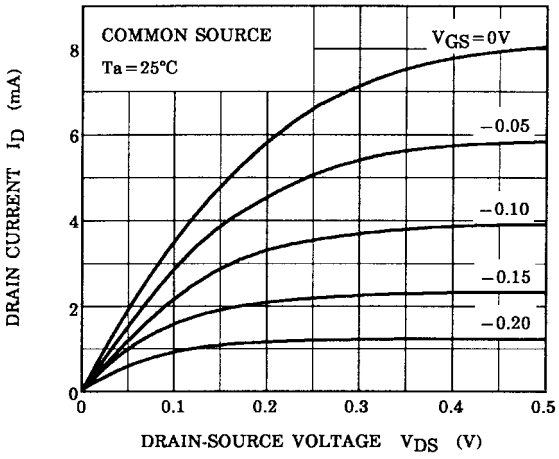
Note 1: I_{DSS} classification GR: 5.0~10.0 mA, BL: 8.0~16.0 mA, Y: 14.0~30.0 mA

Note 2: Concition of the typical value I_{DSS} = 15 mA

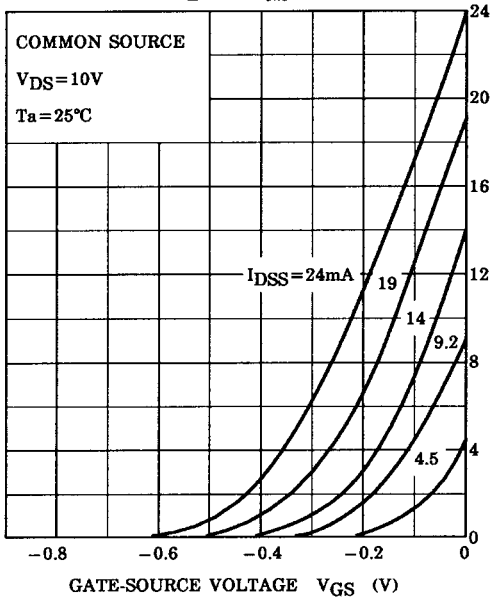
$I_D - V_{DS}$



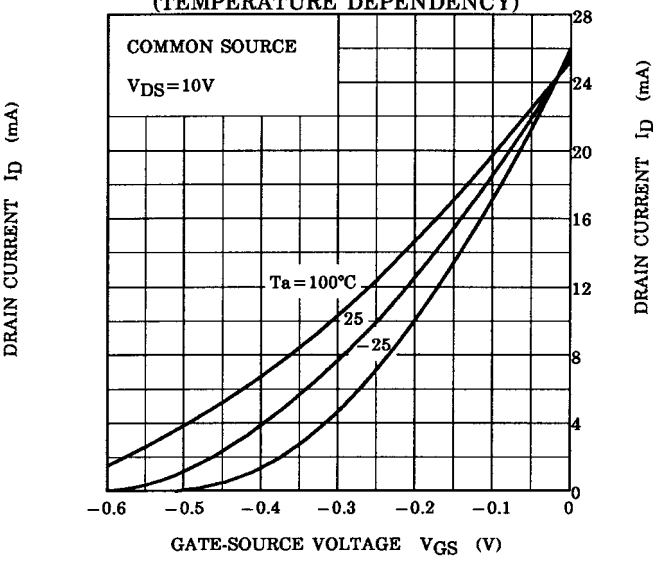
$I_D - V_{DS}$ (LOW VOLTAGE REGION)



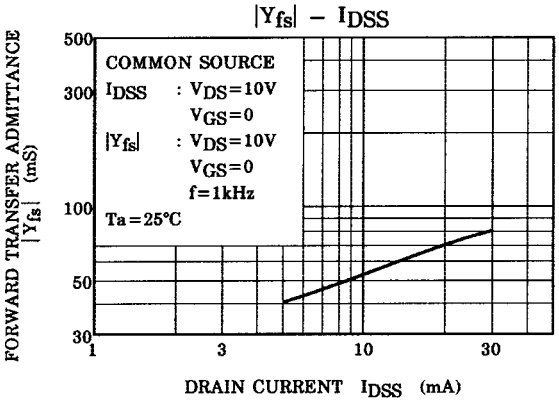
$I_D - V_{GS}$



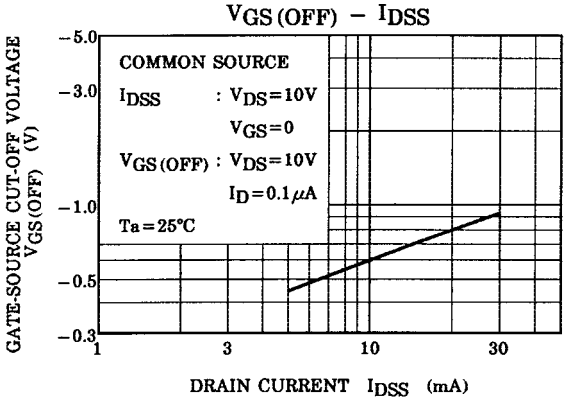
$I_D - V_{GS}$ (TEMPERATURE DEPENDENCY)



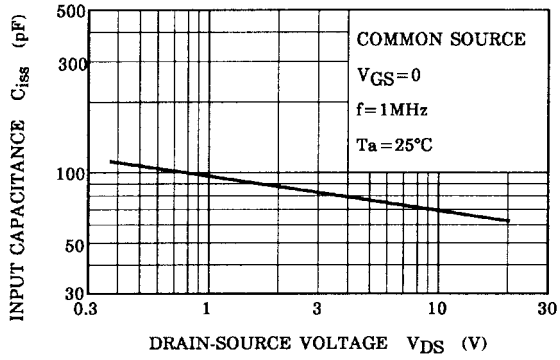
$|Y_{fs}| - I_{DSS}$



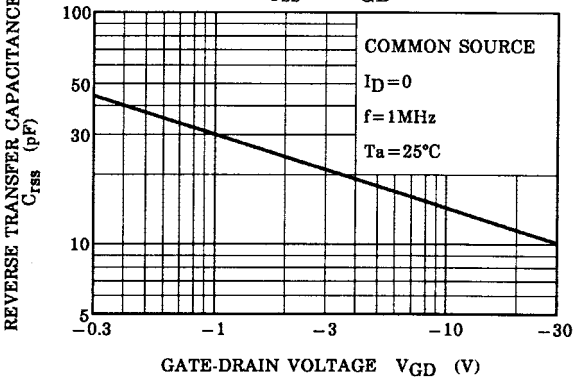
$V_{GS\,(OFF)} - I_{DSS}$



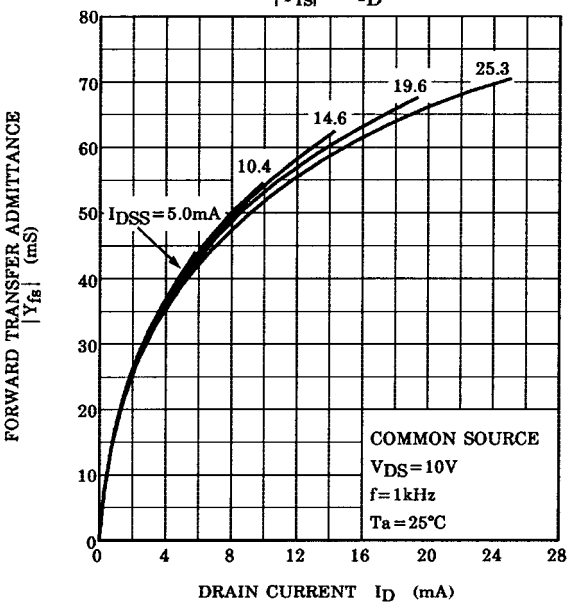
C_{iss} – V_{DS}



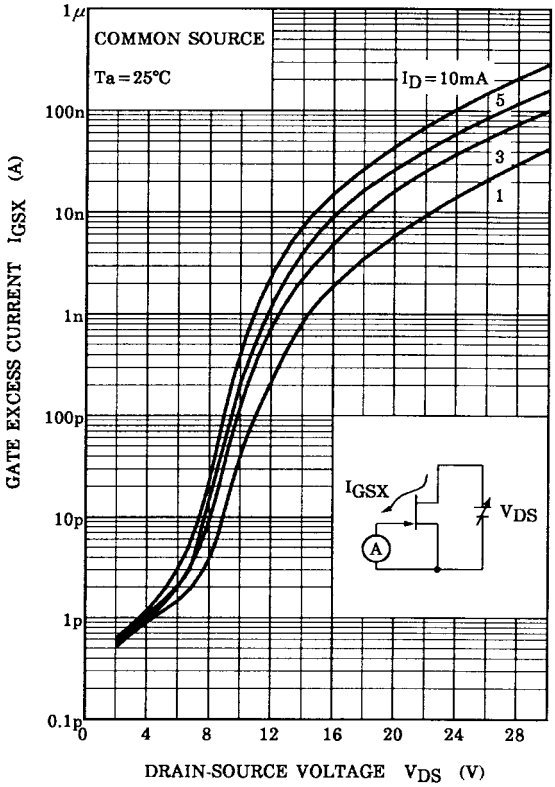
C_{rss} – V_{GD}



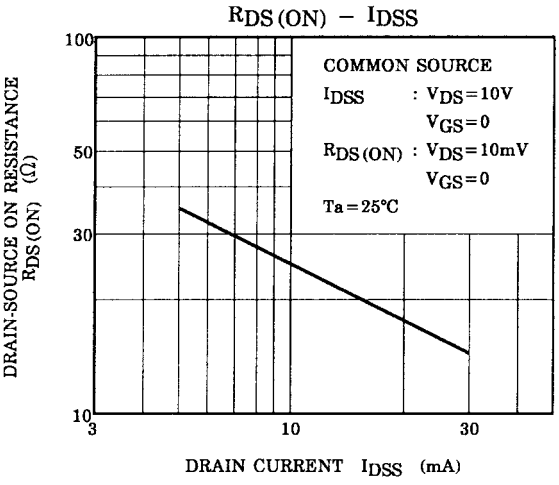
$|Y_{fs}|$ – I_D



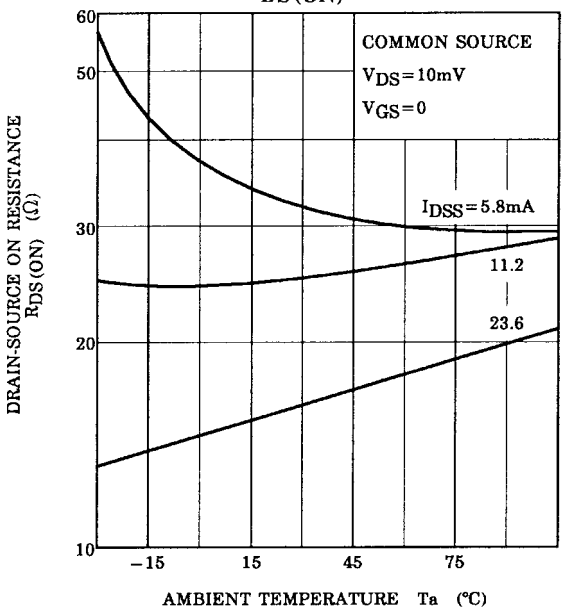
I_{GSX} – V_{DS}



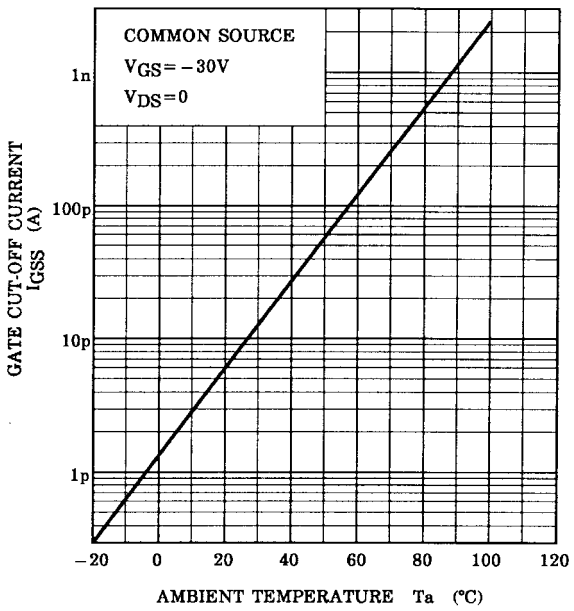
$R_{DS(ON)}$ – I_{DSS}



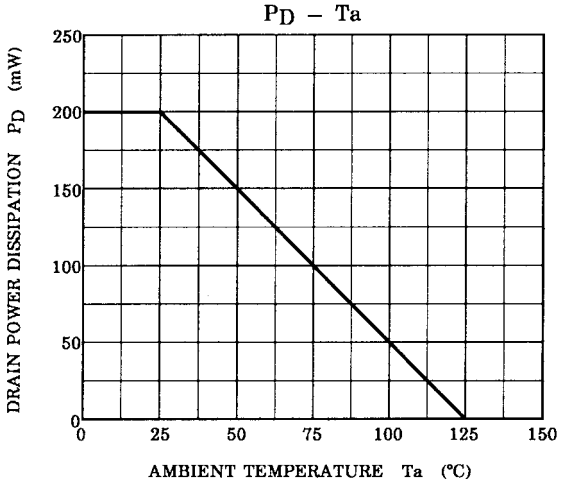
$R_{DS\,(ON)}$ – Ta



I_{GSS} – Ta



P_D – Ta



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